

Thermal resistance, junction-to-ambient	$R_{\theta JA}$	22	25.2	$^{\circ}\text{C/W}$
Thermal resistance, junction-to-case	$R_{\theta JC}$	1.5	3.15	$^{\circ}\text{C/W}$

Thermal Characteristic

Diode pulse current	I_{spulse}	8		A
Continuous diode forward current	I_S	5		A
Storage temperature	T_{stg}	-22~120		$^{\circ}\text{C}$
Operating junction temperature	T_J	-22~120		$^{\circ}\text{C}$
Derate above 52 $^{\circ}\text{C}$		0.2	0.3	$\text{W}/^{\circ}\text{C}$
Power dissipation	P^D	0.9	0.4	W
Avalanche energy, single pulse S	E_{AS}	80		μmJ
Pulsed drain current I	I_{DM}	8		A
Continuous drain current	I_D	5		A
Gate-source voltage	V_{GS}	± 30		V
Drain-source voltage	V_{DS}	1000		V